

TO-220F Plastic-Encapsulated Transistors

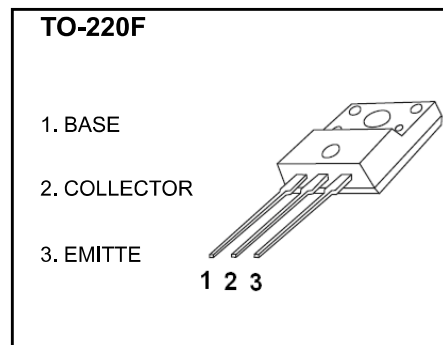
3DA5371 TRANSISTOR (NPN)

FEATURES

- Breakdown Voltage High
- Reverse Cut-off Current Small
- Saturation Voltage Low
- Power dissipation

$P_{CM} : 1.5W (T_a=25.)$

$25 W (T_c=25.)$



MAXIMUM RATINGS ($T_a=25^{\circ}C$ unless otherwise noted)

Symbol Para	meter	Value	Unit
V_{CBO}	Collector-Base Voltage	180	V
V_{CEO}	Collector-Emitter Voltage	160	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current -Continuous	1.5	A
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature	-55-150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=1mA, I_E=0$ 180				V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10mA, I_B=0$ 160				V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$ 6				V
Collector cut-off current	$I_{CBO} V$	$V_{CB}=180V, I_E=0$			10	μA
Emitter cut-off current	$I_{EBO} V$	$V_{EB}=6V, I_C=0$			10	μA
DC current gain	$h_{FE} *$	$V_{CE}=5V, I_C=200mA$ 60			240	
Collector-emitter saturation voltage	$V_{CE(sat)} *$	$I_C=500mA, I_B=50mA$			1	V
Transition frequency	$f_T V$	$V_{CE}=10V, I_C=50mA$ 50				MHz

*Pulse test: $t_p \leq 300\mu S, \delta \leq 0.02.$

CLASSIFICATION OF h_{FE}

Rank O		R
Range	60-140	100-240